



**TRANSMITTAL LETTER**  
**(General - Patent Pending)**

Docket No.  
**PHUS010631**

In Re Application Of: **Letavic et al.**

Serial No.  
**10/015,640**

Filing Date  
**12/10/2001**

Examiner  
**Ngo, N.**

Group Art Unit  
**2814**

Title: **HIGH FREQUENCY HIGH VOLTAGE SILICON-ON-INSULATOR DEVICE WITH MASK VARIABLE INVERSION CHANNEL AND METHOD FOR FORMING THE SAME**

TO THE ASSISTANT COMMISSIONER FOR PATENTS:


Transmitted herewith is: **Amendment in 4 pages**

**Separate Markup Sheet in 2 pages**  
**2 Return Receipt Postcards**

in the above identified application.

- ☒ No additional fee is required.
- ☐ A check in the amount of \_\_\_\_\_ is attached.
- ☒ The Assistant Commissioner is hereby authorized to charge and credit Deposit Account No. **500999** as described below. A duplicate copy of this sheet is enclosed.
- ☐ Charge the amount of \_\_\_\_\_
- ☒ Credit any overpayment.
- ☒ Charge any additional fee required.

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Signature

Dated: **November 25, 2002**

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I certify that this document and fee is being deposited on **11/25/2002** with the U.S. Postal Service as first class mail under 37 C.F.R. 1.8 and is addressed to the Assistant Commissioner for Patents, Washington, D.C. 20231.

  
Signature of Person Mailing Correspondence

**Dorothea Rubbone**

Typed or Printed Name of Person Mailing Correspondence

CC:



DOCKET NO. PHUS010631

2814  
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Amend 13  
y/Johnson  
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Letavic et al.	)	Examiner: Ngo, N.
	)	
Application No.: 10/015,640	)	Art Unit: 2814
	)	
Filed: 12/10/2001	)	
	)	
For: HIGH FREQUENCY HIGH VOLTAGE	)	
SILICON-ON-INSULATOR DEVICE WITH	)	
MASK VARIABLE INVERSION CHANNEL	)	
AND METHOD FOR FORMING THE SAME	)	

Commissioner for Patents  
Washington D.C. 20231

AMENDMENT

Sir:

In response to the Office Action of September 10, 2002, please amend the application as follows:

In the Claims

Claims 1 and 8 have been amended as follows as indicted in the attached Separate

Markup Sheet:

1. (Amended) A high frequency semiconductor device having a shifted doping profile,  
comprising:

B) a buried oxide layer formed over a semiconductor substrate; and

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